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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

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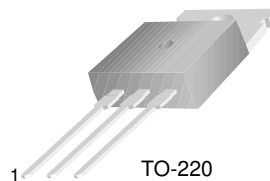
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



KSD73

Low Frequency High Power Amplifier

- Collector-Base Voltage : $V_{CBO} = 100V$
- Collector Current : $I_C = 5A$
- Collector Dissipation : $P_C = 30W$ ($T_C=25^\circ C$)



TO-220
1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	5	A
P_C	Collector Dissipation ($T_C=25^\circ C$)	30	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ C$

Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 1mA, I_E = 0$	100			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 20mA, I_B = 0$	60			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1mA, I_C = 0$	5			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 100V, I_E = 0$			5	mA
h_{FE}	DC Current Gain	$V_{CE} = 10V, I_C = 1.0A$	70		240	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 5A, I_B = 0.5A$			1.5	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_C = 0.3A$		20		MHz
$V_{BE(on)}$	Base-Emitter ON Voltage	$V_{CE} = 10V, I_E = 1.0A$		0.75		V

h_{FE} Classification

Classification	O	Y
h_{FE}	70 ~ 140	120 ~ 240

Typical Characteristics

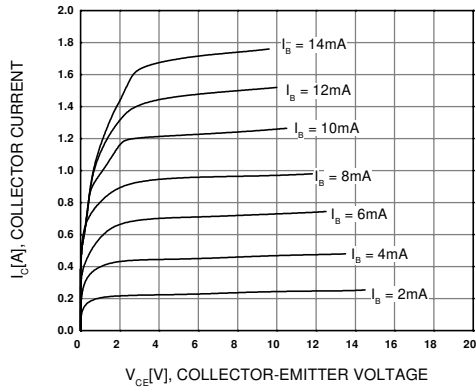


Figure 1. Static Characteristic

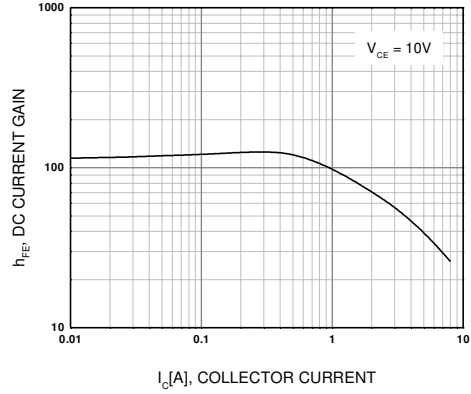


Figure 2. DC current Gain

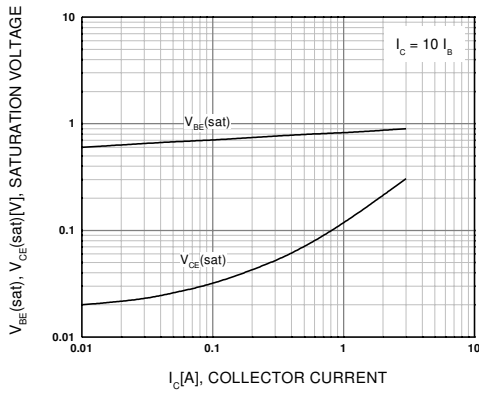


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

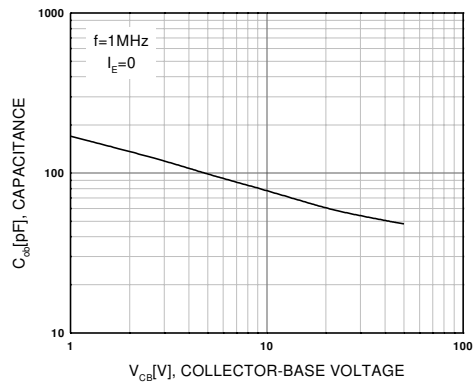


Figure 4. Collector Output Capacitance

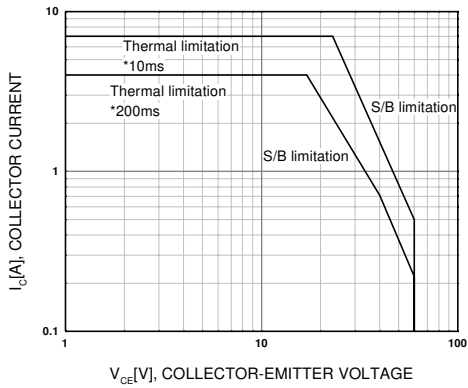


Figure 5. Safe Operating Area

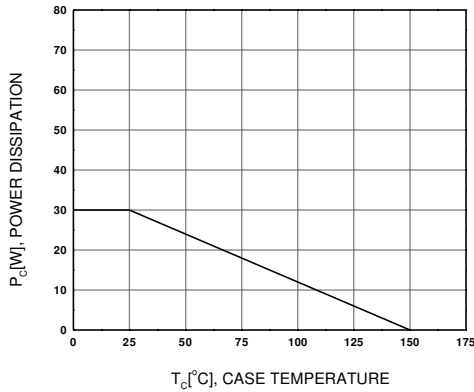
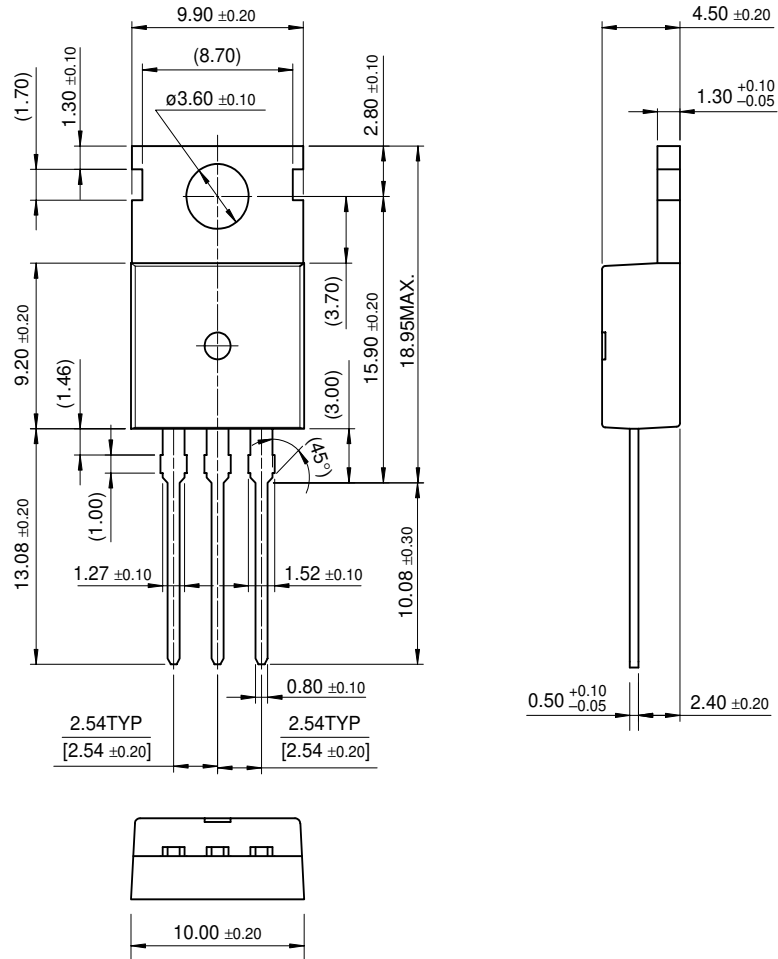


Figure 6. Power Derating

Package Dimensions

KSD73

TO-220



Dimensions in Millimeters

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